

Front-end of the STS/MUCH-XYTER2, full-size prototype ASIC for CBM experiment

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We present a complete design of the analog front-end of the STS/MUCH-XYTER2 ASIC, a full-size prototype chip for the Silicon Tracking System (based on double-sided silicon strip sensors) and Muon Chamber (gas sensors) detectors at the Compressed Baryonic Matter experiment at FAIR, Germany. The charge processing channel includes a charge sensitive amplifier, shaper amplifiers forming two signal paths for timing measurement via a fast discriminator and low-noise amplitude measurement by a 5-bit continuous-time ADC with digital peak detector. Harsh environment, different operating conditions and constraints posed by two target detector applications required flexibility and careful design to meet extended system-wise requirements. The presented circuit implements switchable shaper peaking time, gain switching and trimming, pulsed reset of the amplifier for increased input charge rate and faster recovery from overload, fail-safe measures and diagnostic modes for wafer-level and in-system testing and calibration. The power consumption is scalable (for STS and MUCH modes) but limited to 12 mW/channel.

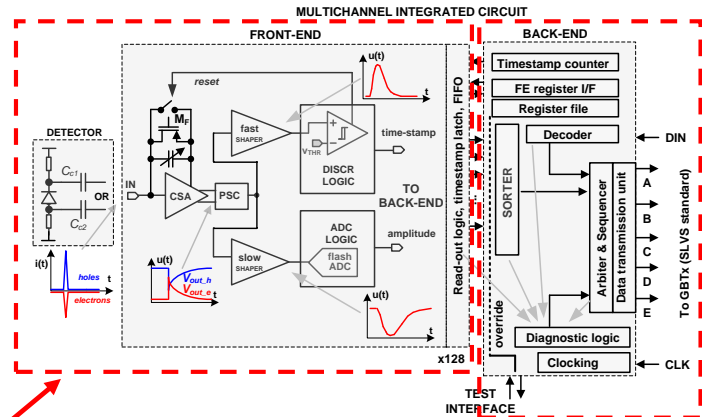


Fig. 1. The simplified architecture of the 128-channel STS/MUCH-XYTER2 ASIC.

This poster is focused on the front-end electronics.

Back-end part is presented in the screen 2.



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Main application requirements:

- multichannel self-triggerred architecture (50 μm pitch),
- deposited charge time and energy measurements,
- average rate of input pulses 250 kHz/channel,
- input charge in the range (electrons and holes):
 - 0.5 fC – 15 fC for the STS mode,
 - 1 fC – 100 fC for the MUCH mode,
- detector capacitance at the order of tens pF,
- low noise ENC < 1000 e⁻ rms at C_{DET} = 30 pF,
- limited power consumption < 10 mW/channel
- good uniformity of analog parameters between channel,
- radiation-hardness property.

Readout front-end architecture:

- input stage: Charge Sensitive Amplifier + Polarity Selection Circuit,
- fast path:
 - optimized to determine the input charge arrival time with the resolution of the order of few ns,
 - built of: CR-RC shaper with $t_p = 40$ ns, discriminator, time-stamp latch, pulse stretcher,
- slow path:
 - optimized for accurate energy measurement:
 - built of: CR-(RC)² based shaper with switchable $t_p = 80, 15, 220, 280$ ns, 5-bit flash ADC, digital peak detector.

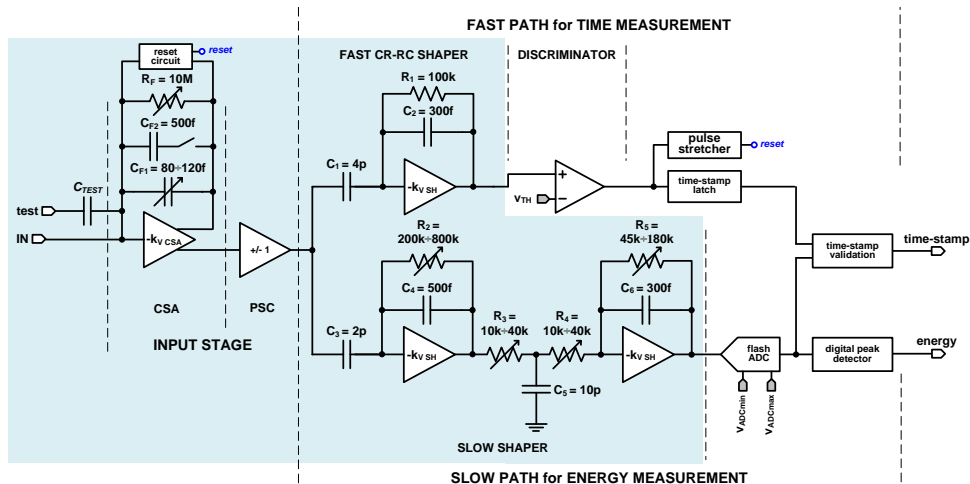


Fig. 2. The simplified architecture of the single readout channel implemented in the STS/MUCH-XYTER2 ASIC.

Charge Sensitive Amplifier:

- based on the direct cascode architecture:
 - input branch current range 0 – 3.9 mA (def. 2 mA),
 - cascode branch current range 0 – 70 μ A (def. 30 μ A)
 - parameters for default settings: voltage gain $k_V = 4.8$ kV/V, GBW = 9.1 GHz, power dissipation $P_{CSA} = 2.7$ mW,
- charge gain: $k_q = 9.4$ mV/fC for STS mode and $k_q = 1.67$ mV/fC for MUCH mode,
- CSA feedback: capacitances C_{FB_STS} , $C_{FB_TRIM1\&2}$ (gain trimming), C_{FB_MUCH} , resistance $R_F \approx 10$ M Ω and reset circuit,
- features:
 - double polarities operation,
 - fast recovery from overload,
 - spark protection,
 - fail-safe operation (C_C failure)
 - crosstalk-proof.

Polarity Selection Circuit:

- based on differential pair architecture.
- single ended voltage gain $k_V = 1$ V/V,
- power dissipation $P_{PSC} = 0.5$ mW

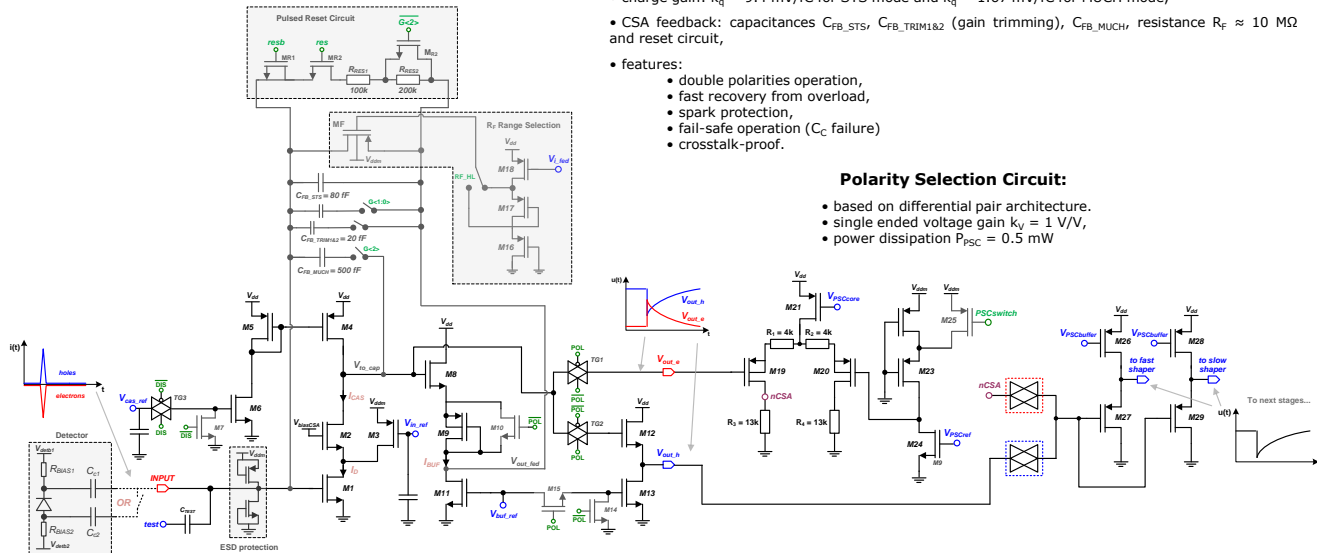


Fig. 3. The input stage architecture details: Charge Sensitive Amplifier (CSA) + Polarity Selection Circuit (PSC).

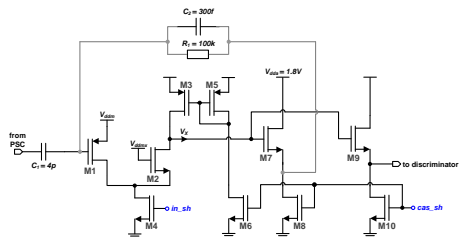


Fig. 4. Shapers' core voltage amplifier architecture.

Shapers' core voltage amplifier:

- based on folded cascode architecture.
- voltage gain $k_V = 2.5 \text{ kV/V}$,
- $\text{GBW} = 1.3 \text{ GHz}$,
- power dissipation $P_{\text{SHcore}} = 0.4 \text{ mW}$.

Fast shaper*:

- peaking time $t_p = 30 \text{ ns}$,
- charge gain $k_q = 84 \text{ mV}$,
- $\text{ENC} = 778 \text{ e}^- \text{ rms}$.

* schematic level simulation, pure detector capacitance model $C_{\text{DET}} = 30 \text{ pF}$.

Slow shaper*:

- peaking time $t_p = 80 \text{ ns}$,
- charge gain $k_q = 40 \text{ mV}$,
- $\text{ENC} = 510 \text{ e}^- \text{ rms}$.

